

# Ling-Xuan Qian

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Ultrahigh-Responsivity, Rapid-Recovery, Solar-Blind Photodetector Based on Highly Nonstoichiometric Amorphous Gallium Oxide. ACS Photonics, 2017, 4, 2203-2211.	3.2	254
2	High-sensitivity $\text{In}_2\text{Ga}_2\text{O}_3$ solar-blind photodetector on high-temperature pretreated c-plane sapphire substrate. Optical Materials Express, 2017, 7, 3643.	1.6	74
3	$\text{In}_2\text{Ga}_2\text{O}_3$ solar-blind deep-ultraviolet photodetector based on annealed sapphire substrate. Vacuum, 2017, 140, 106-110.	1.6	63
4	Simultaneously improved sensitivity and response speed of $\text{In}_2\text{Ga}_2\text{O}_3$ solar-blind photodetector via localized tuning of oxygen deficiency. Applied Physics Letters, 2019, 114, .	1.5	50
5	Effects of Ta incorporation in $\text{La}_2\text{O}_3$ gate dielectric of InGaZnO thin-film transistor. Applied Physics Letters, 2014, 104, .	1.5	45
6	Comprehensively Improved Performance of $\text{In}_2\text{Ga}_2\text{O}_3$ Solar-Blind Photodetector Enabled by a Homojunction with Unique Passivation Mechanisms. ACS Applied Materials & Interfaces, 2021, 13, 40837-40846.	4.0	45
7	High Performance Flexible Visible-Blind Ultraviolet Photodetectors with Two-Dimensional Electron Gas Based on Unconventional Release Strategy. ACS Nano, 2021, 15, 8386-8396.	7.3	38
8	$\text{In}_2\text{Ga}_2\text{O}_3$ solar-blind deep-ultraviolet photodetector based on a four-terminal structure with or without Zener diodes. AIP Advances, 2016, 6, .	0.6	32
9	Improved Detectivity of Flexible a-InGaZnO UV Photodetector via Surface Fluorine Plasma Treatment. IEEE Electron Device Letters, 2019, 40, 1646-1649.	2.2	28
10	Improved Performance of Amorphous InGaZnO Thin-Film Transistor With $\text{Ta}_2\text{O}_5$ Gate Dielectric by Using La Incorporation. IEEE Transactions on Device and Materials Reliability, 2014, 14, 1056-1060.	1.5	26
11	Ultra-sensitive $\text{In}_2\text{Ga}_2\text{O}_3$ Solar-Blind Photodetector with High-Density Al@Al <sub>2</sub> O <sub>3</sub> Core-Shell Nanoplasmonic Array. Advanced Optical Materials, 2022, 10, .	3.6	18
12	Effects of Ta incorporation in $\text{Y}_2\text{O}_3$ gate dielectric of InGaZnO thin-film transistor. Applied Physics Letters, 2016, 109, .	1.5	15
13	Improved Performance of Amorphous InGaMgO Metal-Semiconductor-Metal Ultraviolet Photodetector by Post Deposition Annealing in Oxygen. IEEE Nanotechnology Magazine, 2018, 17, 29-35.	1.1	15
14	Improved Performance of Amorphous InGaZnO Thin-Film Transistor by Hf Incorporation in $\text{La}_2\text{O}_3$ Gate Dielectric. IEEE Transactions on Device and Materials Reliability, 2018, 18, 333-336.	1.5	13
15	Improved Performance of InGaZnO Thin-Film Transistor With HfLaO Gate Dielectric Annealed in Oxygen. IEEE Transactions on Device and Materials Reliability, 2014, 14, 177-181.	1.5	11
16	Anti-reflective porous Ge by open-circuit and lithography-free metal-assisted chemical etching. Applied Surface Science, 2021, 546, 149083.	3.1	9
17	A low-frequency noise model with carrier generation-recombination process for pentacene organic thin-film transistor. Journal of Applied Physics, 2013, 114, 044503.	1.1	8
18	Determination of the Band Alignment of $\text{In}_2\text{Ga}_2\text{O}_3/\text{InGaMgO}$ Heterojunction for High-Electron Mobility Transistor Application. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700251.	1.2	7

#	ARTICLE	IF	CITATIONS
19	Amorphous InGaMgO Ultraviolet Photo-TFT with Ultrahigh Photosensitivity and Extremely Large Responsivity. <i>Materials</i> , 2017, 10, 168.	1.3	6
20	Tailoring the Band Alignment of Ga <sub>x</sub> Zn <sub>1-x</sub> O/InGaZnO Heterojunction for Modulation-Doped Transistor Applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1800332.	0.8	4
21	Band alignment and interfacial chemical structure of the HfLaO/InGaZnO <sub>4</sub> heterojunction investigated by x-ray photoelectron spectroscopy. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 145106.	1.3	2
22	Influence of Ar/O <sup>2</sup> ratio during IGZO deposition on the electrical characteristics of a-IGZO TFT with HfLaO gate dielectric. , 2013, , .		1
23	Solar-blind deep-ultraviolet photodetector based on the $\text{In}^{2+}\text{Ga}^{2+}\text{O}^{3+}$ thin film grown on annealed c-plane sapphire substrate. , 2016, , .		1
24	$\text{In}^{2+}\text{Ga}^{2+}\text{O}^{3+}$ solar-blind deep-ultraviolet photodetector based on annealed sapphire substrate. , 2016, , .		1
25	MoO <sup>3x</sup> -based bipolar switching ReRAM fabricated by atomic layer deposition. , 2017, , .		1
26	Localized surface plasmon-enhanced photodetection in $\text{In}^{2+}\text{Ga}^{2+}\text{O}^{3+}$ solar-blind photodetector with Sn nanoparticles array. , 2022, , .		1
27	The effects of O <sup>2</sup> annealing on the characteristics of IGMO-based UV photodetector. , 2016, , .		0
28	Influence of sensitization on the surface properties of PbSe thin films. , 2017, , .		0